600V N-Channel MOSFET

Lead Free Package and Finish

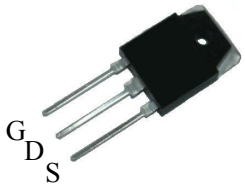
BV_{DSS}	$R_{DS(ON),typ.}$	I_D
600V	120mΩ	36A

General Features

- Advanced Planar Process
- $R_{DS(ON),typ.}$=120 mΩ@V_{GS}=10V
- Low Gate Charge Minimize Switching Loss
- Rugged Poly silicon Gate Structure

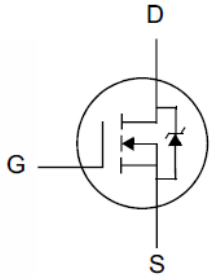
Applications

- BLDC Motor Driver
- Electric Welder
- High Efficiency SMPS



TO-3P

Package Not to Scale



Ordering Information

Part Number	Package	Brand
PTW36N60	TO-3P	

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	PTW36N60	Unit
V_{DSS}	Drain-to-Source Voltage	600	V
V_{GSS}	Gate-to-Source Voltage	±30	
I_D	Continuous Drain Current	36	A
	Continuous Drain Current @ Tc=100℃	23	
I_{DM}	Pulsed Drain Current at V_{GS}=10V[2,4]	80	
E_{AS}	Single Pulse Avalanche Energy	5000	mJ
dv/dt	Peak Diode Recovery dv/dt[3]	5.0	V/ns
P_D	Power Dissipation	650	W
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	℃
T_J& T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PTW36N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.19	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	

Electrical Characteristics

OFF Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	--	--	V	V_{GS}=0V, I_D=250uA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	V_{DS}=600V, V_{GS}=0V
		--	--	125		V_{DS}=480V, V_{GS}=0V, T_J =125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	V_{GS}=+30V, V_{DS}=0V
		--	--	-100		V_{GS}=-30V, V_{DS}=0V

ON Characteristics

T_J =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	120	180	mΩ	V_{GS}=10V, I_D=18A
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250uA
g_{FS}	Forward Transconductance	--	39	--	S	V_{DS} =15V, I_D=18A

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	7400	--	pF	V_{GS}=0V, V_{DS}=25V, f=1.0MHz
C_{rss}	Reverse Transfer Capacitance	--	40	--		
C_{oss}	Output Capacitance	--	650	--		
Q_g	Total Gate Charge	--	150	--	nC	V_{DD}=300V, I_D=36A, V_{GS}=0 to 10V
Q_{gs}	Gate-to-Source Charge	--	40	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	40	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	55	--	nS	V_{DD}=300V, I_D=36A, V_{GS}= 10V R_G=10Ω
t_{rise}	Rise Time	--	95	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	150	--		
t_{fall}	Fall Time	--	65	--		

Source-Drain Body Diode Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current[2]	--	--	36	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current[2]	--	--	80		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	I_S=36A, V_{GS}=0V
trr	Reverse recovery time	--	500	--	ns	V_{GS}=0V ,I_F=36A, di_F/dt=100A/μs
Qrr	Reverse recovery charge	--	4.5	--	uC	

Note:

[1] T_J=+25℃ to +150℃ .
[2] Silicon limited current only.
[3] Package limited current.
[4] Repetitive rating; pulse width limited by maximum junction temperature.
[5] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

Figure 1. Maximum Transient Thermal Impedance

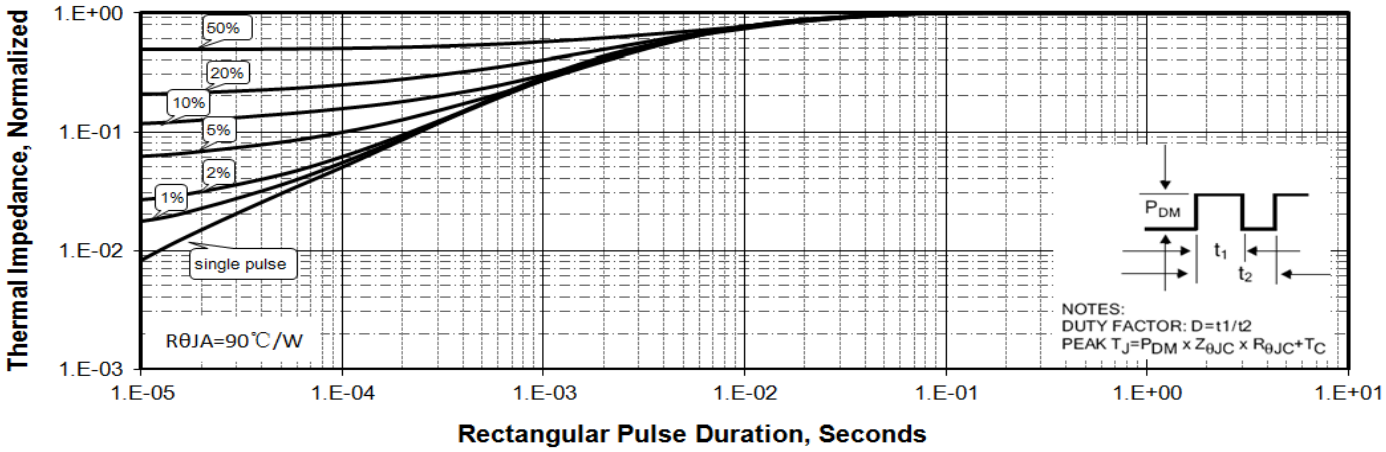


Figure 2 . Max. Power Dissipation vs Case Temperature

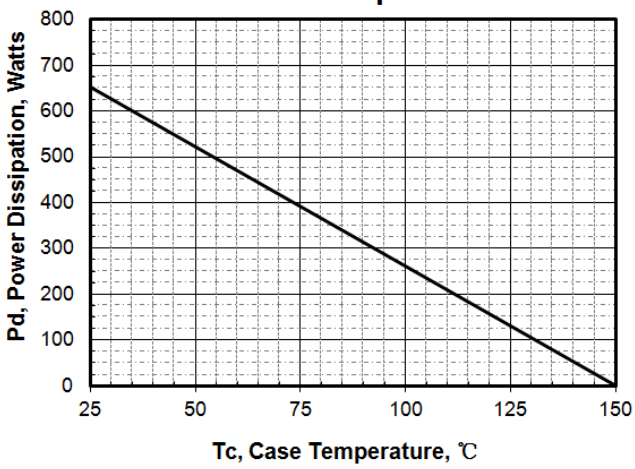


Figure 3 .Maximum Continuous Drain Current vs Tc

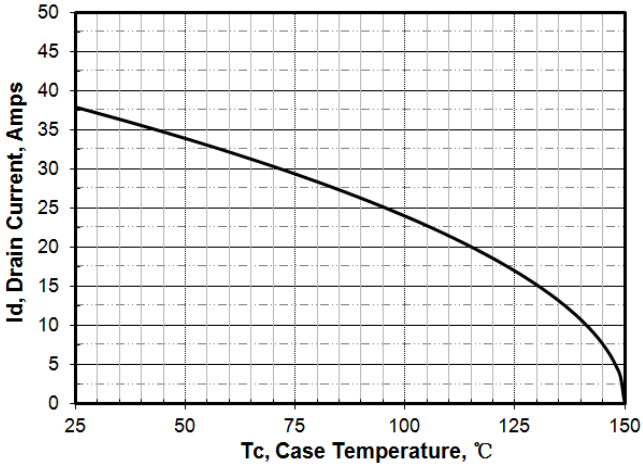


Figure 4. Output Characteristics

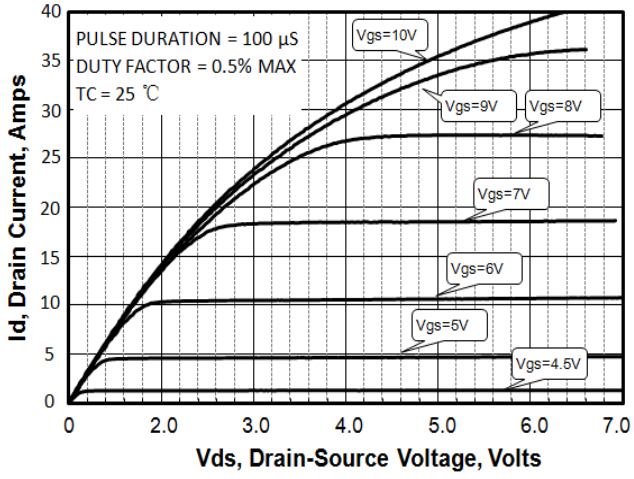
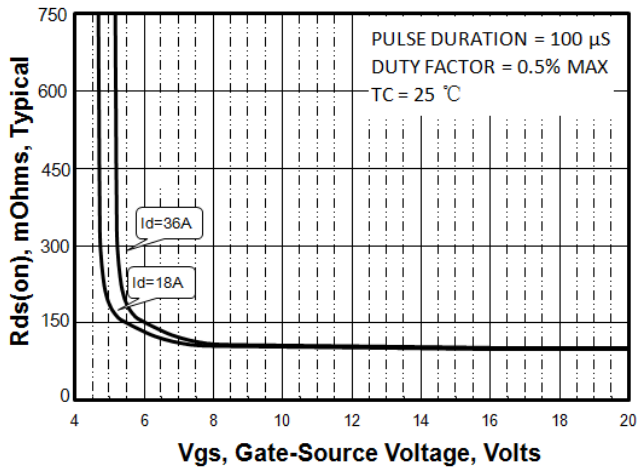


Figure 5. Rdson vs Gate Voltage



Typical Characteristics(Cont.)

Figure 6. Peak Current Capability

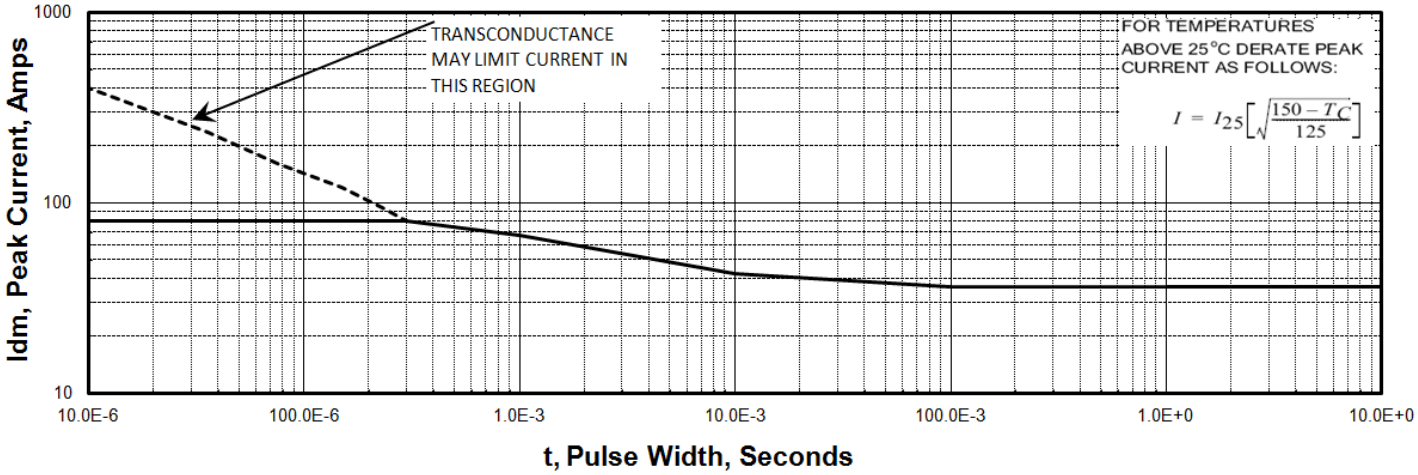


Figure 7. Transfer Characteristics

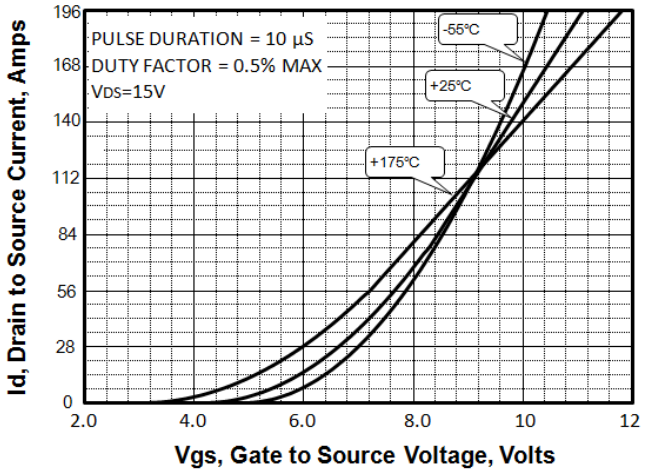


Figure 8. Unclamped Inductive Switching Capability

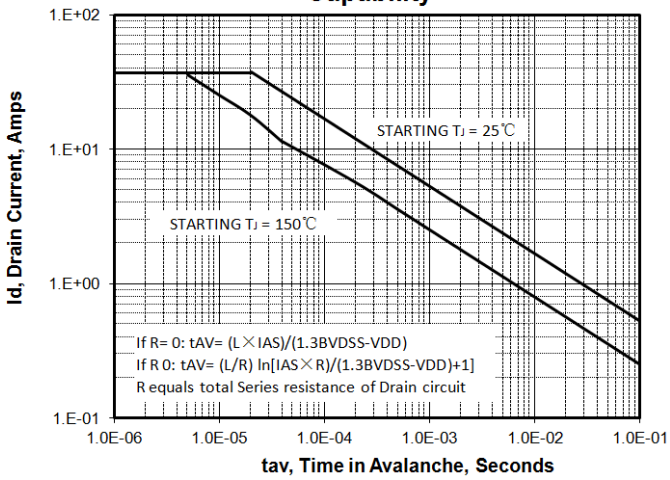


Figure 9. Drain to Source ON Resistance vs Drain Current

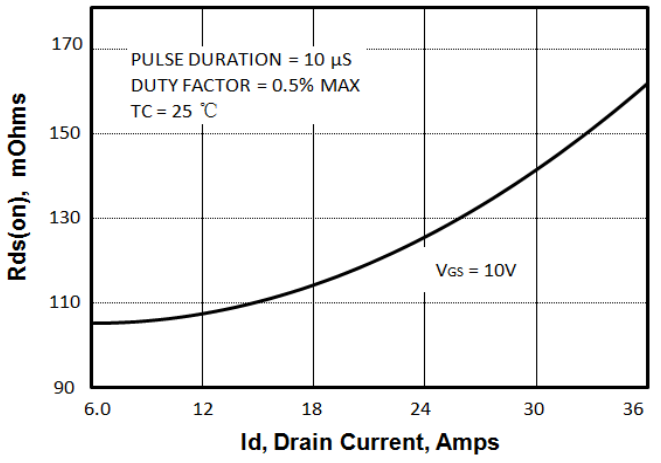
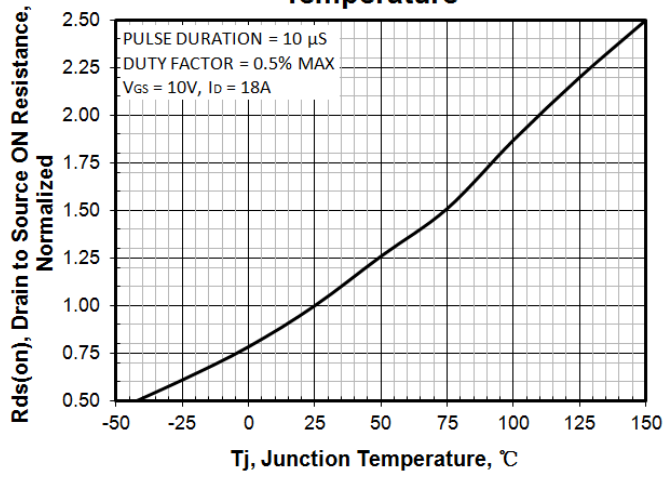


Figure 10. Rdson vs Junction Temperature



Typical Characteristics(Cont.)

Figure 11.Breakdown Voltage vs Temperature

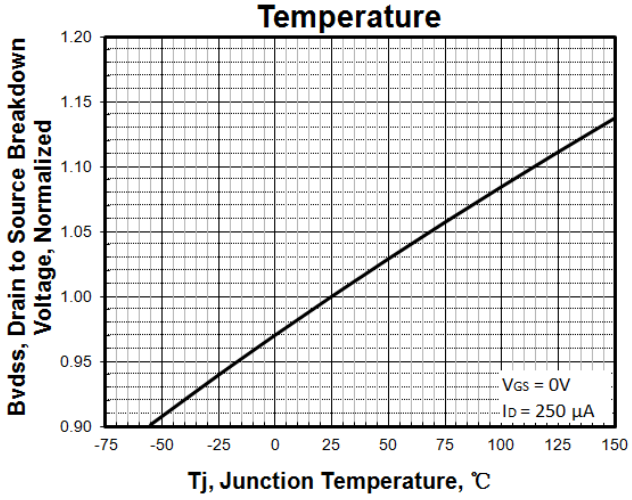


Figure 12.Threshold Voltage vs Temperature

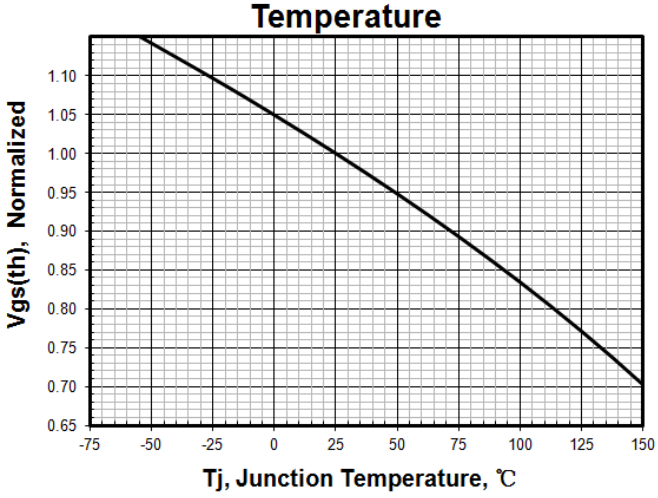


Figure 13 . Maximum Safe Operating Area

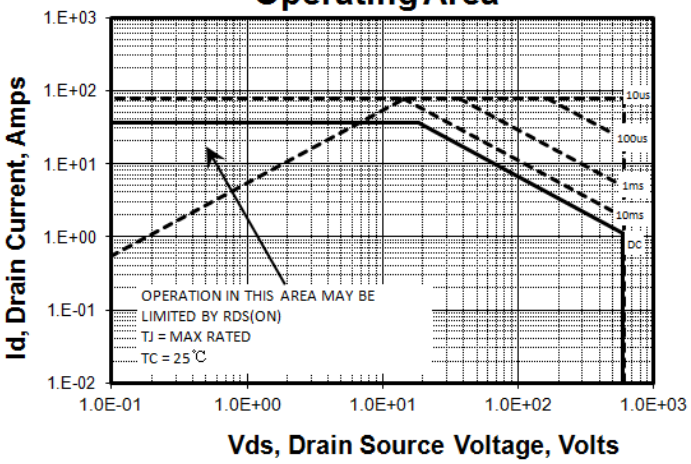


Figure 14. Capacitance vs Vds

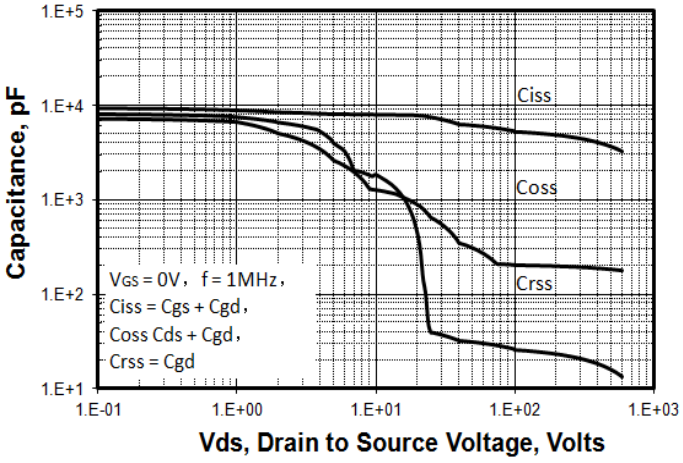


Figure 15 .Typical Gate Charge

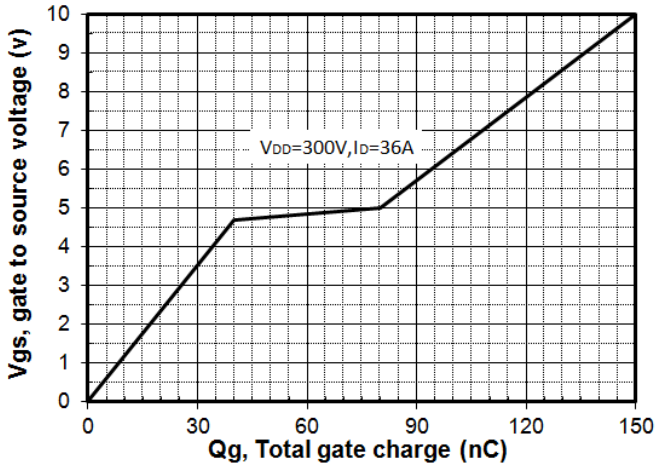
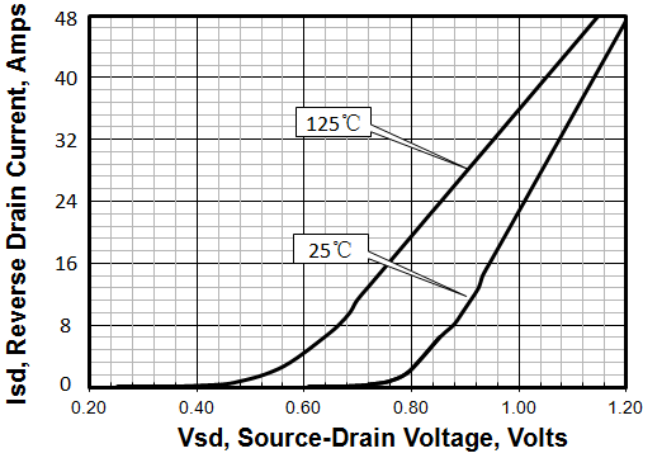


Figure 16.Body Diode Transfer Characteristics



Test Circuits and Waveforms

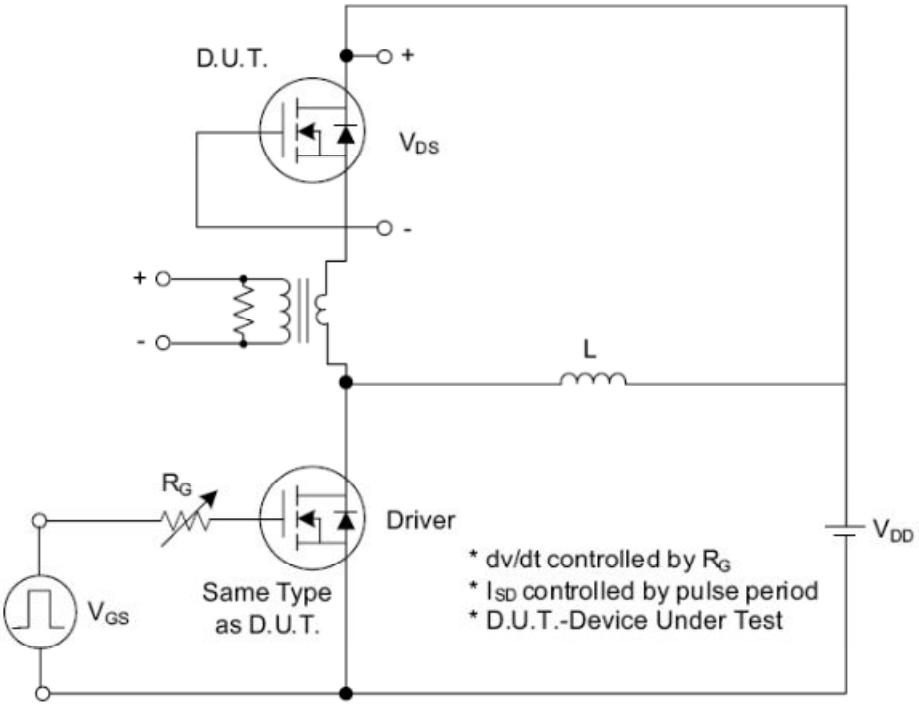


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

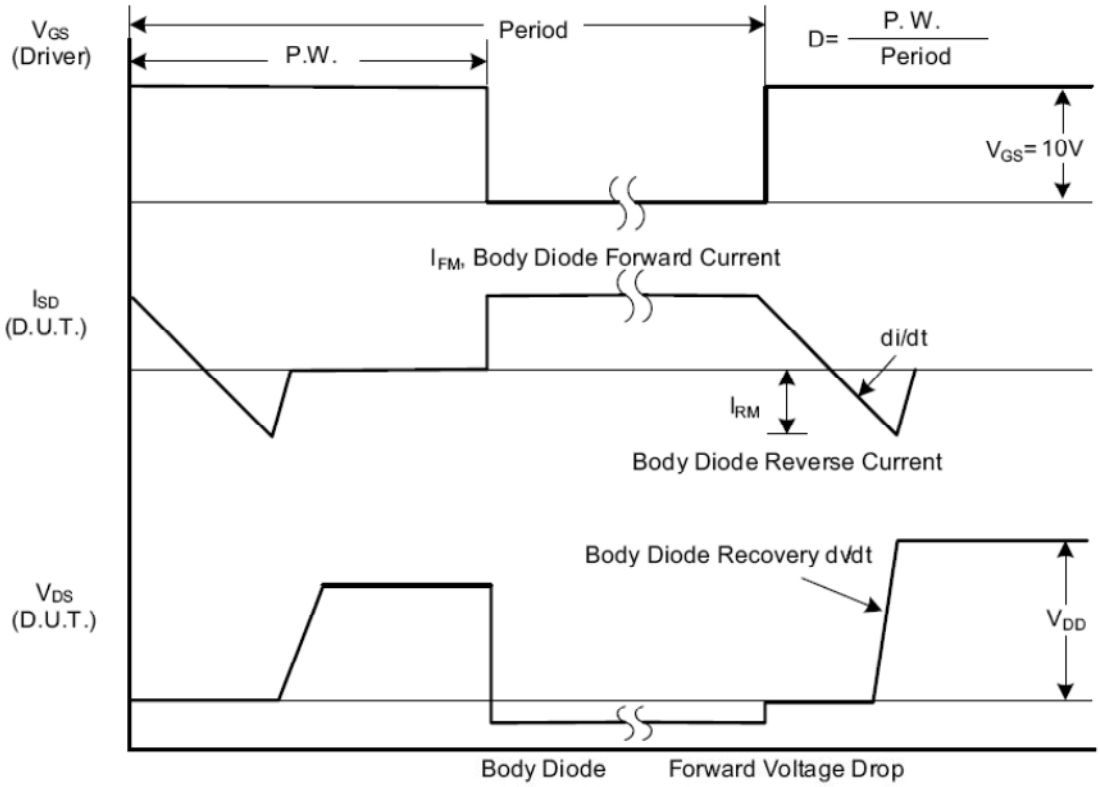


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

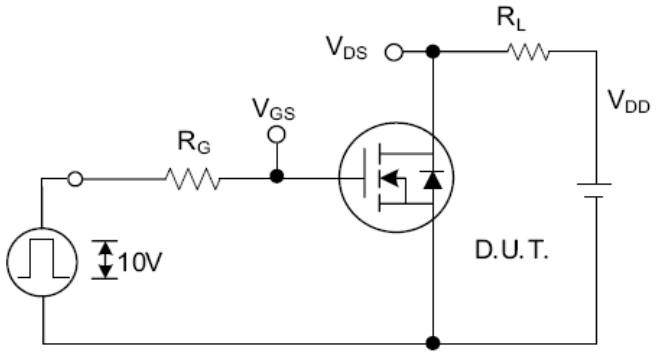


Fig. 2.1 Switching Test Circuit

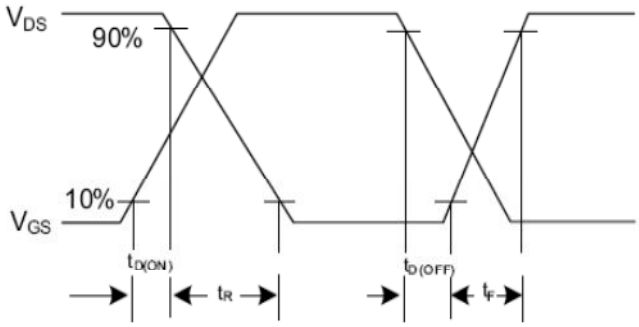


Fig. 2.2 Switching Waveforms

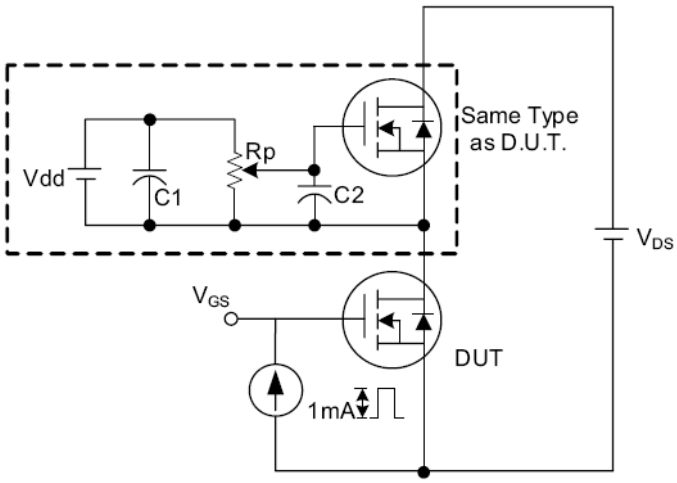


Fig. 3 . 1 Gate Charge Test Circuit

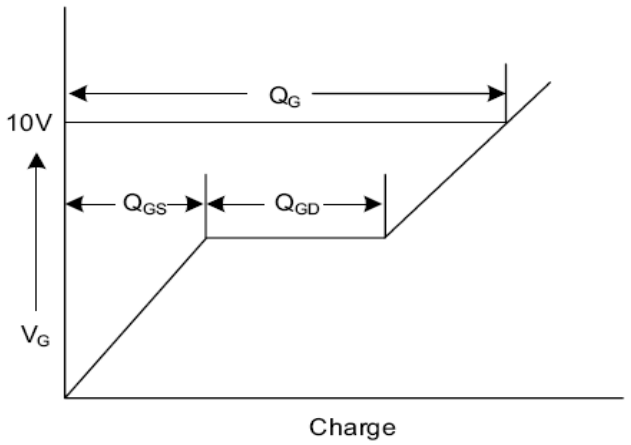


Fig. 3 . 2 Gate Charge Waveform

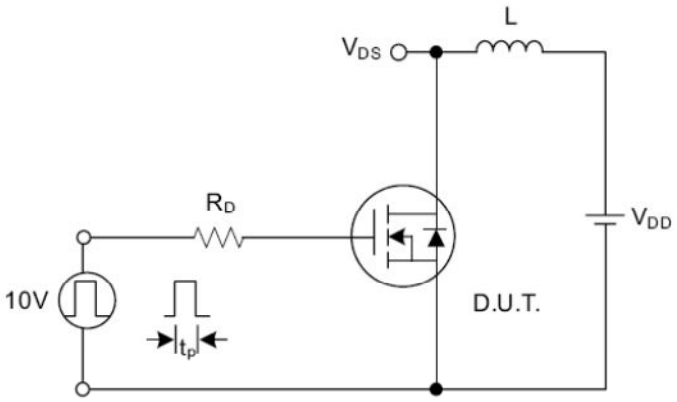


Fig. 4.1 Unclamped Inductive Switching Test Circuit

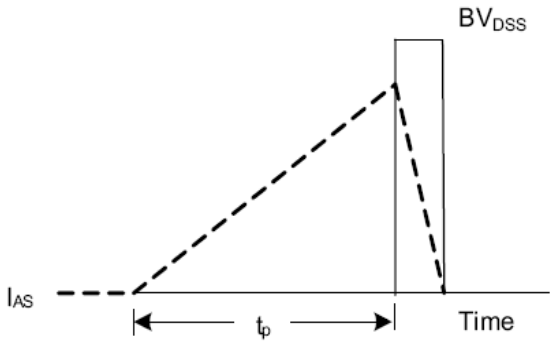


Fig. 4.2 Unclamped Inductive Switching Waveforms

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   b. support or sustain life,
   c. whose failure to perform when properly used in accordance with instructions for used provided in the labeling, can be reasonably expected to result in significant injury to the user.
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